

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI5463EDC-T1-E3

For any questions, you can email us directly: sales@integrated-circuit.com



Si5463EDC

Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

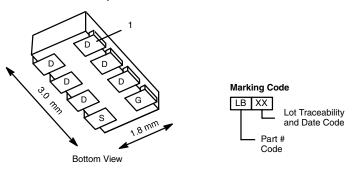
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 20	$0.062 \text{ at V}_{GS} = -4.5 \text{ V}$	- 5.1		
	0.068 at V _{GS} = - 3.6 V	- 4.9		
	0.085 at V _{GS} = - 2.5 V	- 4.4		
	0.120 at V _{GS} = - 1.8 V	- 3.7		

FEATURES

- Halogen-free According to IEC 61249-2-21 **Available**
- ESD Protected^b 5000 V







Ordering Information: Si5463EDC-T1-E3 (Lead (Pb)-free)

Si5463EDC-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Drain Current /T 150 °C\2	T _A = 25 °C	I _D	- 5.1	- 3.8		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 3.7	- 2.7	Δ.	
Pulsed Drain Current		I _{DM}	- 15		Α	
Continuous Source Current ^a		I _S	- 1.9	- 1.0		
Mariana Baran Birata di a	T _A = 25 °C	P _D	2.3	1.25	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.2	0.65	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		90	
Soldering Recommendations (Peak Temperature) ^{c, d}			260		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
A	t ≤ 5 s	- R _{thJA}	45	55		
Maximum Junction-to-Ambient ^a	Steady State		84	100	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	20	25		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. When using HBM. The MM rating is 300 V.
- c. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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Datasheet of SI5463EDC-T1-E3 - MOSFET P-CH 20V 3.8A 1206-8

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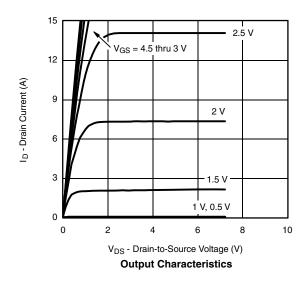
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45			٧		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 1.5			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 16 V, V _{GS} = 0 V		- 1	μΑ			
		V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C			- 5			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 15			Α		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 4.0 A		0.051	0.062			
		V _{GS} = - 3.6 V, I _D = - 3.5 A		0.056	0.068			
		$V_{GS} = -2.5 \text{ V}, I_D = -3.0 \text{ A}$		0.070	0.085	Ω		
		V _{GS} = - 1.8 V, I _D = - 1.5 A		0.100	0.120			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 4.0 A		10		S		
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.0 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.75	- 1.2	V		
Dynamic ^b								
Total Gate Charge	Q_g			9.7	15	nC		
Gate-Source Charge	Q _{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.0 \text{ A}$		2.7				
Gate-Drain Charge	Q _{gd}			1.4				
Turn-On Delay Time	t _{d(on)}			1.85	2.5	- μs		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		3.2	4.5			
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, $V_{GEN}=$ - 4.5 V, $R_G=6~\Omega$		1.9	2.5			
Fall Time	t _f			3.2	4.5			

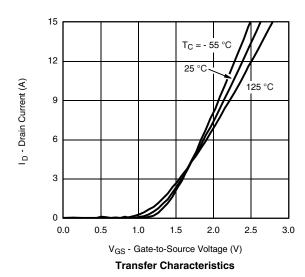
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





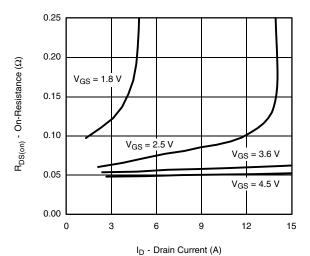




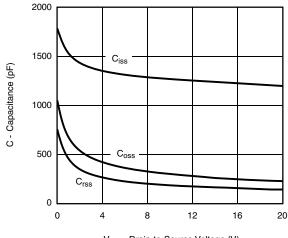
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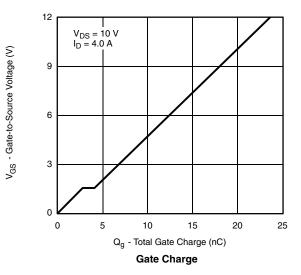


On-Resistance vs. Drain Current

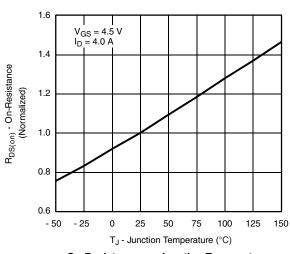


V_{DS} - Drain-to-Source Voltage (V)

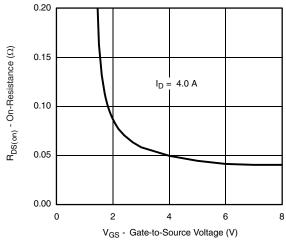




20 10 Is - Source Current (A) T_J = 150 °C T_J = 25 °C 0.1 0.01 0.0 0.2 0.6 1.0 12 0.4 0.8 V_{SD} - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

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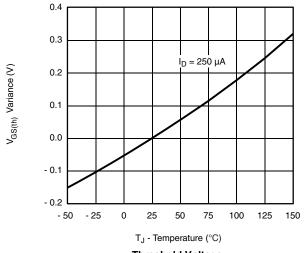
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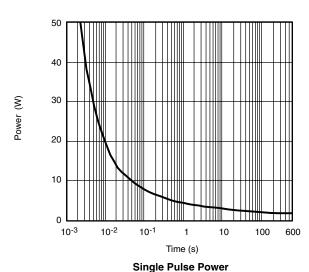
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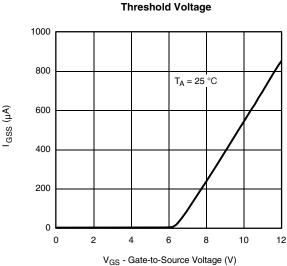
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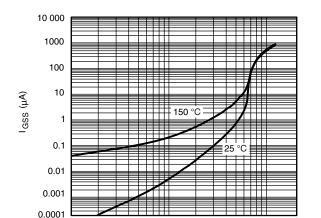
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted











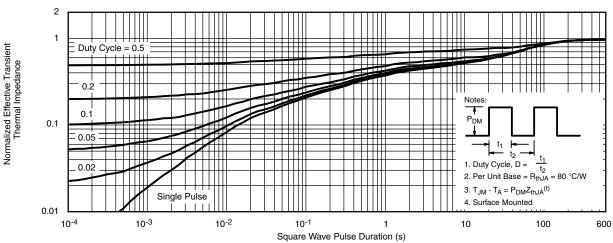
0.10

Gate-Source Voltage vs. Gate Current

V_{GS} - Gate-to-Source Voltage (V)

Gate-Source Voltage vs. Gate Current

20



Normalized Thermal Transient Impedance, Junction-to-Ambient



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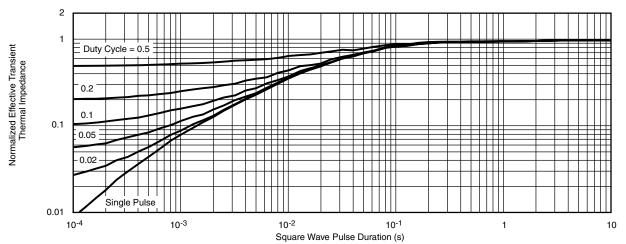
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71364.

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